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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/900,043	07/09/2001	Takahiro Yajima	35.C15541	3915
5514	7590 06/17/2003			
FITZPATRICK CELLA HARPER & SCINTO			EXAMINER	
	EFELLER PLAZA RK, NY 10112  DANG, TRUNG			
			ART UNIT	PAPER NUMBER
			2823	

DATE MAILED: 06/17/2003

Please find below and/or attached an Office communication concerning this application or proceeding.

	•	Application No.	Applicant(s)	- Ww
••		09/900,043	YAJIMA ET AL.	
	Office Action Summary	Examiner	Art Unit	
	-	Trung Q. Dang	2823	
-	- The MAILING DATE of this communication a			ress
Period fo	r Reply	,	•	
THE N - Extension after S - If the p - If NO p - Failure - Any re	ORTENED STATUTORY PERIOD FOR REF ALLING DATE OF THIS COMMUNICATION sions of time may be available under the provisions of 37 CFR (IX (6) MONTHS from the mailing date of this communication. period for reply specified above is less than thirty (30) days, a reperiod for reply is specified above, the maximum statutory period for reply within the set or extended period for reply will, by state ply received by the Office later than three months after the mail patent term adjustment. See 37 CFR 1.704(b).	I. 1.136(a). In no event, however, pply within the statutory minimur d will apply and will expire SIX ( ute, cause the application to bec	may a reply be timely filed  of thirty (30) days will be considered timely.  MONTHS from the mailing date of this corone ABANDONED (35 U.S.C. § 133).	nmunication.
1) 🗌	Responsive to communication(s) filed on _			
2a) <u></u> □	This action is <b>FINAL</b> . 2b)⊠	This action is non-final.		
3)∏ Dispositio	Since this application is in condition for allocalosed in accordance with the practice under on of Claims			merits is
4) 🖾	Claim(s) 1-10 is/are pending in the applicati	on.		
4	a) Of the above claim(s) is/are withdo	awn from consideratio	1.	
5)🛛 (	Claim(s) <u>6-10</u> is/are allowed.			
6)🖂 (	Claim(s) <u>1-5</u> is/are rejected.			
7) 🗌 (	Claim(s) is/are objected to.			
8) 🗌 (	Claim(s) are subject to restriction and	or election requiremen	t.	
Application	on Papers			
9)∐ T	he specification is objected to by the Examir	ner.		
10)∐ T	he drawing(s) filed on is/are: a)□ acc	epted or b) objected to	by the Examiner.	
	Applicant may not request that any objection to	Ŧ.,	• • • • • • • • • • • • • • • • • • • •	
11) 🗌 T	he proposed drawing correction filed on	is: a)∏ approved b	disapproved by the Examiner	:
	If approved, corrected drawings are required in	• •		
12) 🗌 T	he oath or declaration is objected to by the E	Examiner.		
riority u	nder 35 U.S.C. §§ 119 and 120			
13)🛛 🗸	Acknowledgment is made of a claim for forei	gn priority under 35 U.	S.C. § 119(a)-(d) or (f).	
a)∑	∄All b)☐ Some * c)☐ None of:			
1	. Certified copies of the priority docume	nts have been received	<b>).</b>	
2	2. Certified copies of the priority document	nts have been received	in Application No	
	B. Copies of the certified copies of the pri application from the International E se the attached detailed Office action for a lis	Bureau (PCT Rule 17.2	(a)).	tage
14) 🗌 Ad	knowledgment is made of a claim for domes	stic priority under 35 U.	S.C. § 119(e) (to a provisional a	pplication).
	☐ The translation of the foreign language pcknowledgment is made of a claim for dome	• •		
ttachment(	s)			
2) Notice	of References Cited (PTO-892) of Draftsperson's Patent Drawing Review (PTO-948) ation Disclosure Statement(s) (PTO-1449) Paper No(s)	5) 🔲 Noti	view Summary (PTO-413) Paper No(s) ce of Informal Patent Application (PTO- r:	
Patent and Trac O-326 (Rev.		Action Summary	Part of Paper No. 12	

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- 1. The indicated allowability of claims 1-5 is withdrawn in view of the newly discovered reference(s) to Li et al (U.S. Pat. 5,942,049) and Otani et al. (EP 658918), all cited by applicants. Rejections based on the newly cited reference(s) follow.
- 2. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 1-5 are rejected under 35 U.S.C. 103(a) as being unpatentable over Li et al. In view of Otani et al.

Li teaches a method for depositing an amorphous silicon film by plasma CVD in a RF glow-discharge system. The reactive gases disclosed are SiH4, H2 (see Table 7 and 8 for the flow rate of SiH4 and hydrogen dilution ratio). The deposition pressure P and electrode spacing d are disclosed in Table 7. From Table 8, selecting a value for the flow rate of SiH4 of 60 sccm (0.06 SLM) within the disclosed range. Accordingly, the flow rate M of H2 is 600 sccm (0.6 SLM) when the hydrogen dilution ratio of 10:1 is selected according to Table 7. From Table 7, selecting a value of 2 torr (approximately 266 Pa) for pressure P and a value of 1cm electrode spacing d. Substitute these values in the equation recited in the pending claim 1 yields:

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$$80 (0.6) + 200 \le 266.1 \le 160 (0.6) + 333$$
$$248 \le 266 \le 429$$

Thus, with respect to the relation as claimed, Li teaching satisfy the equation claimed in claim 1. Li differs from the claims in not disclosing that the substrate is employed as one electrode in the RF glow-discharge apparatus. However, Otani teaches a RF plasma - CVD reactors with internal electrodes wherein substrate S1 is mounted on electrode 2 and hence employed as one of electrode opposite to RF electrode 3 (see Fig. 1). Thus, it would have been obvious to one of ordinary skill in the art to mount the substrate in Li's process on one of the electrode in the RF plasma-CVD reactor as suggested by Otani because such practice is conventional in the art, and the application of a known technique to make the same would have been within the level of an artisan. As for claim 2, substituting the values of P, d, and L (total flow rates of SiH4 and H2 = 0.6 SLM + 0.06 SLM = 0.66 SLM) to the equation yields:

$$67 (0.66) + 200 \le 266 \le 147 (0.66) + 333$$
  
 $244 \le 266 \le 430$ 

Thus, claim 2 is met by Li.

3. The following is an examiner's statement of reasons for allowance:

Claims 6-10 are allowable over prior art of record because none of prior art teaches or suggests the relation as claimed, which involves volume V of the discharge space.

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Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

4. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Trung Dang whose telephone number is (703) 308-2548. The examiner can normally be reached on weekdays from 9:00 AM to 5:30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri, can be reached on (703) 306-2794. The fax phone number for this Group is (703) 305-3432 or (703) 308-7725.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the Group receptionist whose telephone number is (703) 308-0956.

Trung Dang

Muy Danz

Primary Examiner, Group 2800

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